

Surface Junction in $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$ Single Crystals

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Abstract

As nature junction geometry of the d-wave cuprate superconductor/insulator/the mixture of s-wave and d-wave cuprate superconductor, the upmost surface junction of intrinsic Josephson junction stack fabricated on $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$ single crystals was measured and discussed. We successfully observed half-integral microwave induced steps as well as integral steps with resistively shunting technology, which shows the evidence of second order supercurrent, consistent with Tanaka's theory.

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Pairing symmetry in the cuprate superconductor is an important and controversial topic. The recent development of phase-sensitive test, combined with the refinement of several other symmetry-sensitive techniques, has for the most part settled this controversy in favor of predominantly d-wave symmetry for a number of optimally hole- and electron-doped cuprates [1]. Especially for $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$ (BSCCO), the phase-sensitive test results suggest that the s-wave component of the order parameter should be vanishingly small [2]. Considering the crystal structure of BSCCO, s-wave and d-wave pair states correspond to two distinct irreducible representations and therefore are not allowed to mix [3]. As a result, BSCCO should be pure d-wave pairing symmetry. However, a few c-axis tunneling experiments between BSCCO and s-wave superconductor Pb (BSCCO/Pb junction) consistently unveiled the finite supercurrent of first order. The results show s-wave component in BSCCO should be small but nonzero [4, 5]. However, the evidence of s-wave is proven only in the uppermost cuprate layer which couples to Pb. The question raised from the contradiction is: Is the s-wave component intrinsic or induced from d-wave state under some special condition? Theoretical studies suggest that s-wave pairing symmetry may be induced in a d-wave superconductor, under certain conditions, by spatial inhomogeneities such as surfaces, interfaces, or defects [6, 7, 8, 9]. Reasonable explanation is that the s-wave component of pairing state exists only in the surface cuprate layer of BSCCO, which is induced from d-wave state by the surface effects.

According to a theory by Tanaka, second order c-axis pair tunneling is possible for a junction between c-axis s-wave and pure d-wave superconductors [10]. In other words, half-integer Shapiro steps should be observable in such a junction under microwave irradiation. In the results of c-axis BSCCO/Pb junctions so far reported, the observed supercurrent is dominantly of first order, and microwave induced Shapiro steps only occur at voltages $V = n\phi_0$. Same results have also been observed in other junctions of similar type [11, 12, 13, 14]. In essence, all the junctions mentioned above are coupled by the c-axis pairing tunneling between s-wave conventional superconductor and the cuprate superconductor with the mixture of s-wave and d-wave pairing symmetry (s/I/s_{id}), which was discussed theoretically in detail [15]. Nevertheless, the c-axis pairing tunneling between the d-wave cuprate superconductor and the cuprate superconductor with the mixture of s-wave and d-wave pairing symmetry (d/I/s_{id}) has not been discussed yet both in theory and experiment. Natural geometry of d/I/s_{id} junction, noteworthy but neglected, is the uppermost surface junction

of intrinsic Josephson junction (IJJ) stack fabricated on BSCCO single crystals, which was discussed in a few papers without consideration of the mixture of s-wave states and d-wave states [16, 17, 18]. In this letter, we report and discuss the measurements of the surface junction and the observation of microwave induced steps with resistively shunting method.

BSCCO single crystals were grown using coating zone technique in a four lamp arc-in aging furnace. After cleaving from a bulk crystal, the fresh surface was deposited with a 70 nm layer of gold to obtain a clean surface between single crystal and normal electrode as well as to protect the surface from any contamination during further process of fabrication and measurements. To make the contact resistance ohmic, the cleaved flake was annealed in fresh O_2 flow for 10 minutes at $600^\circ C$, then it was fixed on Si substrate by Polyimide. With conventional photolithography and Ar ion etching, one mesa with a-b plane sizes of $6 \times 6 \text{ } \mu m^2$ covered with gold and photoresist was formed. The junction number in the stack is controlled by the etching time and rate. Finally a layer of SiO₂ was deposited as insulator to protect and separate the mesa. After lift-off, one electrode was connected to the top gold of the mesa, while two other electrodes were connected to the ground plane of the mesa. All the transport measurements described below were carried out with three-probe configuration.

In our experiments, the samples were measured in a liquid helium Dewar flask. Shown in Fig. 1 is the typical $I-V$ curve of the samples. The multiple quasi-particle branches were developed with the increase of bias current. The junction number is counted as 20 corresponding to the number of the branches. The critical current I_c of most junctions is nearly 1.5 mA at 9.2 K except one, the critical current I_c^0 of which is only 0.11 mA, one magnitude order smaller than the majority. The $I-V$ curve of this novel junction is magnified and shown as the inset of main figure. Its supercurrent is a little slantwise due to the linear contact resistance. This junction disappeared when the temperature rose to $T_c^0 = 30 K$ (35% T_c , T_c is the critical temperature of the bulk crystal.) Doh et al. proved by progressively ion-beam etching experiment that the novel junction is the uppermost surface junction which forms by the uppermost two cuprate layers [17]. The d-wave states in cuprate superconductor may induce to s-wave states by spatial inhomogeneities such as surfaces, interfaces, or defects. As a result, the pairing symmetry of the uppermost cuprate layer changes from d-wave states to s[±] id mixed states with broken time-reversal symmetry due to the effect of surface. Moreover, the superconductivity of the uppermost cuprate layer is also suppressed.

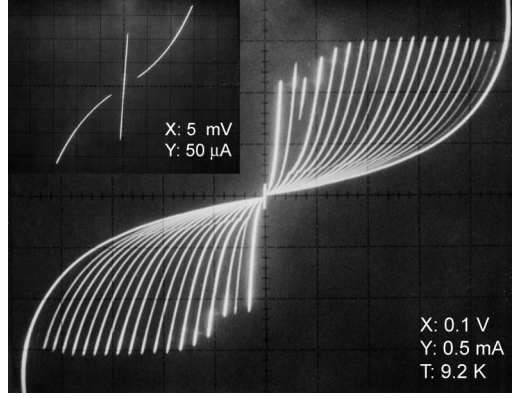


FIG. 1: I - V characteristics of the intrinsic Josephson stack fabricated on BSCCO. The inset is the magnified figure of junction with the minimum critical current I_c^0 .

Consequently, the critical temperature and critical current of the surface junction with the structure of $d/I/s+id$ are greatly suppressed in comparison with the conventional $d/I/d$ IJJ.

The characteristics of critical current of the surface junction varied with temperature $I_c - T$ was measured and shown in Fig. 2. As comparison, $I_c - T$ of conventional IJJ is also shown as the inset of Fig. 2. the solid line in the inset is theoretical calculation of $I_c - T$ for c -axis $d/I/d$ junction by Tanaka etc [15]. The experimental result is consistent with it. However, the evident deviation was found in the surface $d/I/s+id$ junction. It can be fitted by abnormal temperature dependence $I_c \propto (T_c - T)^2$ instead of $I_c \propto T_c - T$ when the temperature is close to T_c .

To investigate the detailed feature of the surface $d/I/s+id$ junction, the microwave response was measured. However, with microwave irradiation at 80 - 100 GHz and lower frequency, no microwave-induced steps were observed. Because Shapiro steps are only observable when $f_{rf} \approx f_p$ in heavy under-damped Josephson junction [19, 20]. And the plasma oscillation frequency f_p of the surface junction is estimated to be 100 GHz from $f_p = (\frac{eJ_c d}{h \epsilon_r \epsilon_0})^{1/2}$, where the critical current density J_c is about 300 A/cm^2 , the thickness of inter-layer d is 12 Å for BSCCO, and the relative dielectric constant ϵ_r is 3.5 [21]. To observe microwave-induced steps, resistively shunted technology was adopted. It has been well established that Shapiro steps can be observable in resistively shunted IJJ [22, 23]. In this letter, we use a gold stripe to shunt the mesa, the inset of Fig. 3 is the schematic figure of the resistively shunted IJJ. For the critical current of the surface junction is lowest in the stack, the surface junction will be firstly shunted. Detailed discussion of resistively shunting

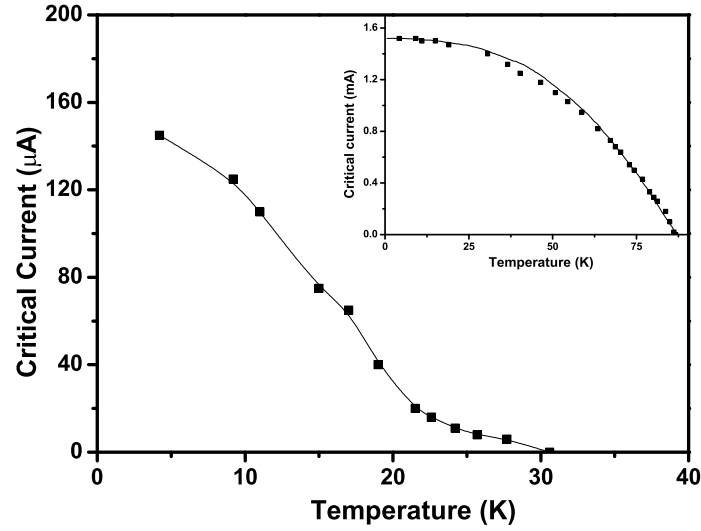


FIG .2: I_c - T characteristics of the surface junction. The inset is I_c - T of conventional intrinsic junction, the solid line in which is theoretical calculation results for c axis $d/I/d$ junction.

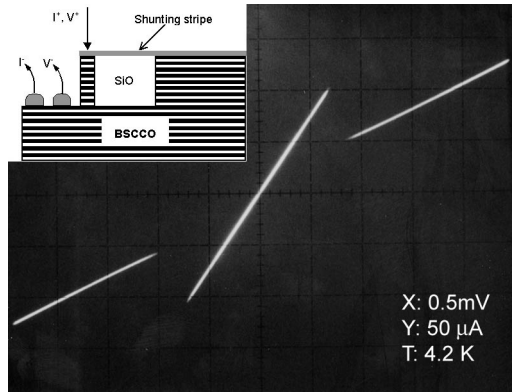


FIG .3: I - V characteristics of resistively shunted surface junction. the inset shows the schematic figure of resistively shunted intrinsic Josephson junction.

theory was published elsewhere [23]. I - V curves shown in Fig. 3 shows typical behavior of RSJ model with a linear contact resistor about 6Ω in series. The resistance is subtracted in the following figures. With microwave irradiation at 99.3 GHz , the microwave-induced steps up to second order were observed and shown in Fig. 4. The interval between the first order steps is 410 V , which fits the Josephson voltage-frequency relationship $V = f \phi_0$ very well. It proves the microwave-induced steps are of the first order supercurrent, which derives from

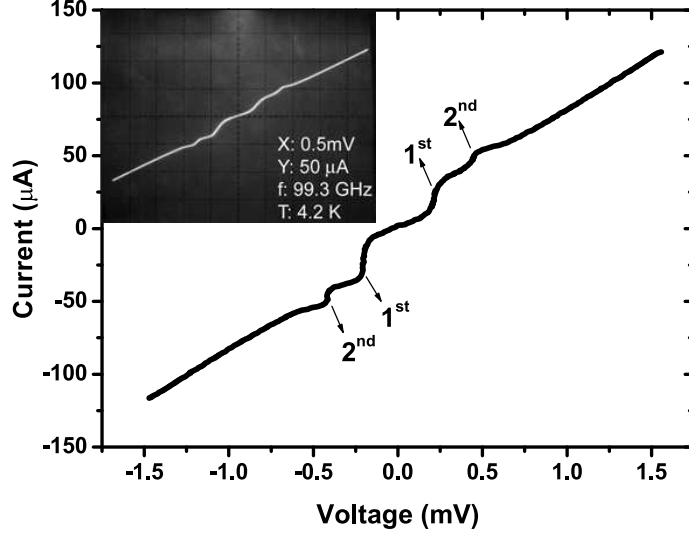


FIG. 4: Integer microwave induced steps of resistively shunted surface junction with the microwave irradiation at 99.3 GHz, the contact resistance is abstracted. the inset shows the original image.

the pair coupling between d-wave component in the surface layer and inner d-wave layer. Fig. 5 shows the microwave response of the resistively shunted surface junction when the frequency of microwave irradiation changed to 89 GHz. Only two steps were obtained, the interval between them is about 185 μ V, which is exactly at $V = 0.5\phi_0$. The half-integral steps prove the existence of the second order supercurrent, which originates from the pair coupling between s-wave component in the surface layer and d-wave in the inner cuprate layer. It is consistent with the prediction of Tanaka [10]. When the power of microwave source increases, the half-integral steps disappear and conventional Shapiro steps appear. It suggests that the second order supercurrent is more sensitive to microwave irradiation than first order supercurrent derived from c-axis pair tunneling between d-wave states. However, because of the low content of s-wave states in the mixture $s+d$ states, the microwave induced half-integral steps were concealed by the conventional Shapiro steps with the increase of the microwave power.

In summary, as natural geometry of d/I/ $s+d$ junction, the surface junction in intrinsic Josephson junctions stack was measured and discussed. The temperature dependence of critical current shows a significantly difference from the intrinsic d/I/d Josephson junction and follows abnormal temperature dependence $I_c \propto (T_c - T)^2$ when the temperature is close to T_c . With resistively shunting method, the surface junction shows typically RSJ

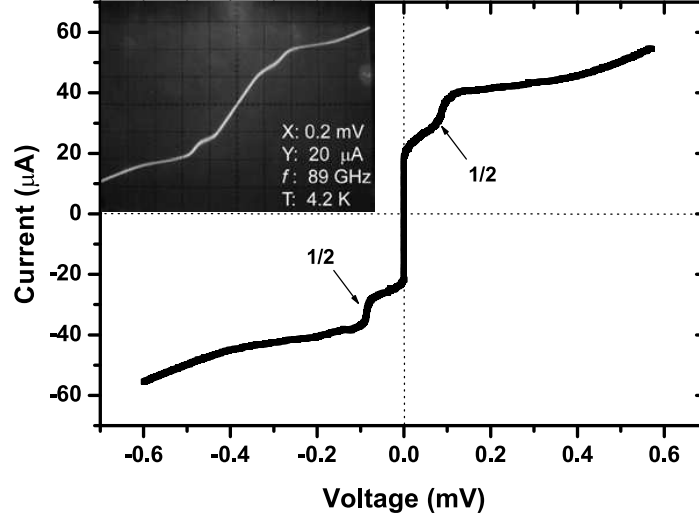


FIG. 5: half-integer microwave induced steps of resistively shunted surface junction with the microwave irradiation at 89 GHz, the contact resistance is abstracted. The inset shows the original image.

model, the half-integer microwave induced steps were observed as well as conventional integral Shapiro steps, which shows the existence of second order supercurrent and supports strongly Tanaka's theory.

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